Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

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Micro Commercial Components

Micro Commercial Components
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CA 91311
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SI2302

N-Channel Enhancement Mode Field Effect Transistor

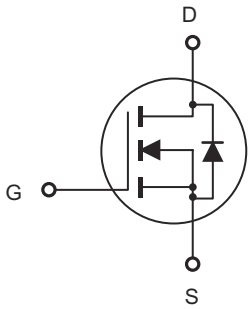
Features

- Halogen free available upon request by adding suffix "-HF"
- 20V,3.0A, $R_{DS(ON)}$=55mΩ @V_{GS}=4.5V
  $R_{DS(ON)}$=82mΩ @V_{GS}=2.5V
- High dense cell design for extremely low $R_{DS(ON)}$
- Rugged and reliable
- Lead free product is acquired
- SOT-23 Package
- Marking Code: S2
- Epoxy meets UL 94 V-0 flammability rating
- Moisture Sensitivity Level 1

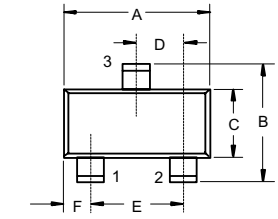
Maximum Ratings @ 25°C Unless Otherwise Specified

Symbol	Parameter	Rating	Unit
V_{DS}	Drain-source Voltage	20	V
I_D	Drain Current-Continuous	3	A
I_{DM}	Drain Current-Pulsed [a]	10	A
V_{GS}	Gate-source Voltage	±8	V
P_D	Total Power Dissipation	1.25	W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient[b]	100	℃/W
T_J	Operating Junction Temperature	-55 to +150	℃
T_{STG}	Storage Temperature	-55 to +150	℃

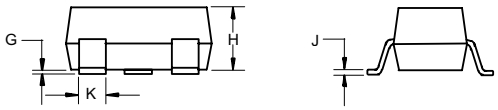
Internal Block Diagram



SOT-23

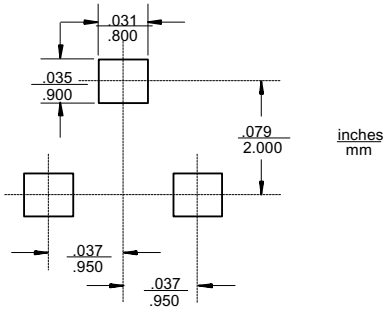


1.GATE
2. SOURCE
3. DRAIN



DIMENSIONS					
	INCHES		MM		
DIM	MIN	MAX	MIN	MAX	NOTE
A	.110	.120	2.80	3.04	
B	.083	.104	2.10	2.64	
C	.047	.055	1.20	1.40	
D	.035	.041	.89	1.03	
E	.070	.081	1.78	2.05	
F	.018	.024	.45	.60	
G	.0005	.0039	.013	.100	
H	.035	.044	.89	1.12	
J	.003	.007	.085	.180	
K	.015	.020	.37	.51	

Suggested Solder Pad Layout



Electrical Characteristics T_A = 25°C unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} = 0V, I_D = 10μA	20			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 20V, V_{GS} = 0V			1	μA
Gate Body Leakage Current, Forward	I_{GSSF}	V_{GS} = 8V, V_{DS} = 0V			100	nA
Gate Body Leakage Current, Reverse	I_{GSSR}	V_{GS} = -8V, V_{DS} = 0V			-100	nA
On Characteristics [c]						
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS} = V_{DS}, I_D = 50μA	0.65		1.2	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = 4.5V, I_D = 3.6A		55	72	mΩ
		V_{GS} = 2.5V, I_D = 3.1A		82	110	mΩ
Forward Transconductance	g_{FS}	V_{DS} = 5V, I_D = 3.6A		8.5		S
Dynamic Characteristics [d]						
Input Capacitance	C_{iss}	V_{DS} = 10V, V_{GS} = 0V, f = 1.0 MHz		237		pF
Output Capacitance	C_{oss}			120		pF
Reverse Transfer Capacitance	C_{rss}			45		pF
Switching Characteristics [d]						
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 10V, I_D = 3.6A, V_{GS} = 4.5V, R_{GEN} = 6Ω		23	45	ns
Turn-On Rise Time	t_r			11	30	ns
Turn-Off Delay Time	$t_{d(off)}$			34	70	ns
Turn-On Fall Time	t_f			36	70	ns
Total Gate Charge	Q_g	V_{DS} = 10V, I_D = 3.6A, V_{GS} = 4.5V		6	10	nC
Gate-Source Charge	Q_{gs}			1.4		nC
Gate-Drain Charge	Q_{gd}			1.8		nC
Drain-Source Diode Characteristics and Maximun Ratings						
Drain-Source Diode Forward Current [b]	I_S				0.94	A
Drain-Source Diode Forward Voltage [c]	V_{SD}	V_{GS} = 0V, I_S = 0.94A			1.2	V

Notes :
a.Repetitive Rating : Pulse width limited by maximum junction temperature.
b.Surface Mounted on FR4 Board, t ≤ 10 sec.
c.Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
d.Guaranteed by design, not subject to production testing.

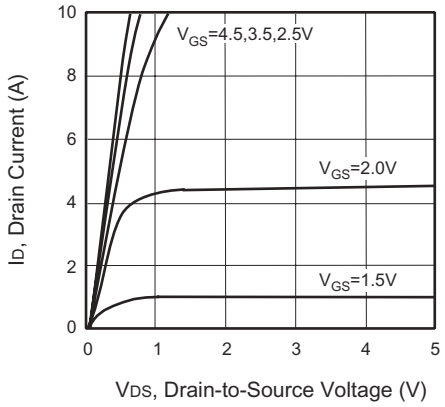


Figure 1. Output Characteristics

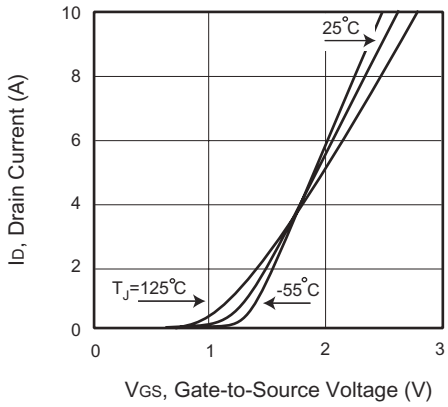


Figure 2. Transfer Characteristics

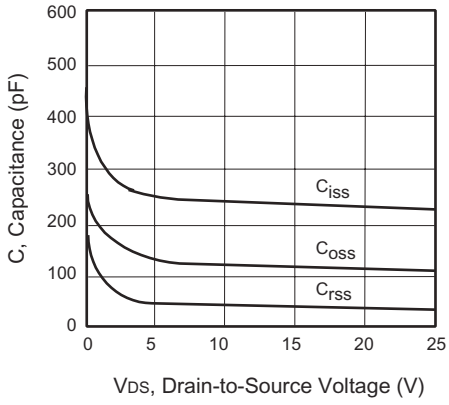


Figure 3. Capacitance

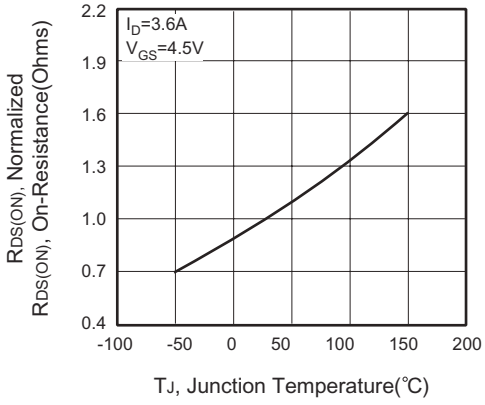


Figure 4. On-Resistance Variation with Temperature

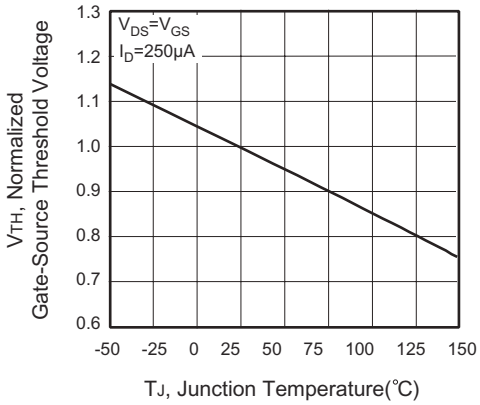


Figure 5. Gate Threshold Variation with Temperature

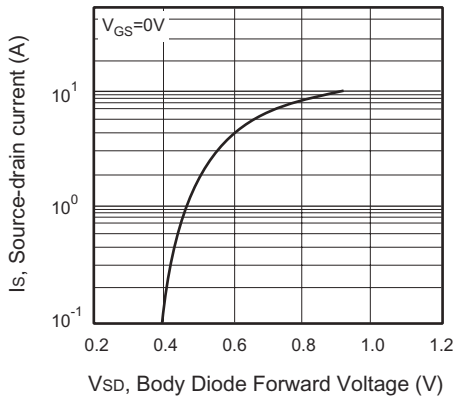


Figure 6. Body Diode Forward Voltage Variation with Source Current

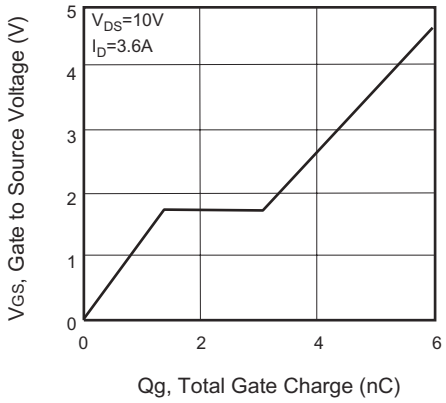


Figure 7. Gate Charge

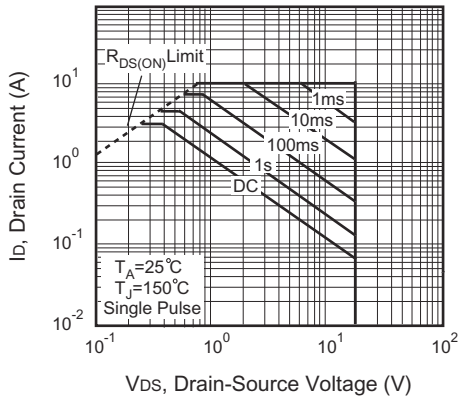


Figure 8. Maximum Safe Operating Area

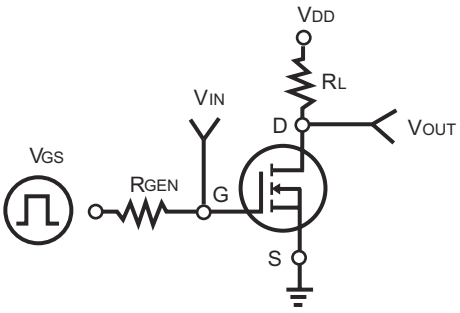


Figure 9. Switching Test Circuit

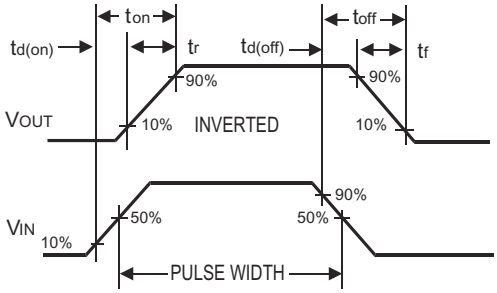


Figure 10. Switching Waveforms

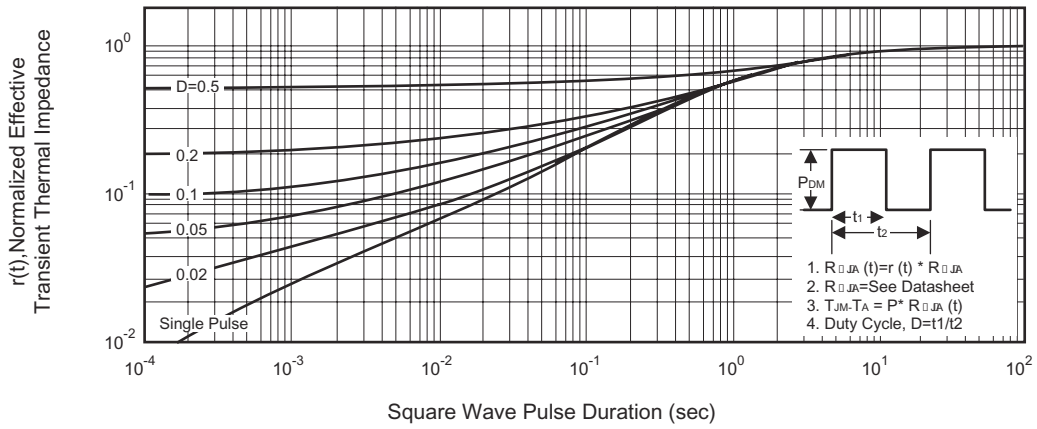


Figure 11. Normalized Thermal Transient Impedance Curve

Ordering Information :

Device	Packing
Part Number-TP	Tape&Reel: 3Kpcs/Reel

Note : Adding "-HF" suffix for halogen free, eg. Part Number-TP-HF